2SA1484

Silicon PNP Epitaxial

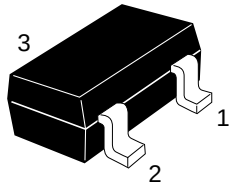
HITACHI

Application

Low frequency amplifier

Outline

MPAK



1. Emitter
2. Base
3. Collector

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	–90	V
Collector to emitter voltage	V_{CEO}	–90	V
Emitter to base voltage	V_{EBO}	–5	V
Collector current	I_C	–100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

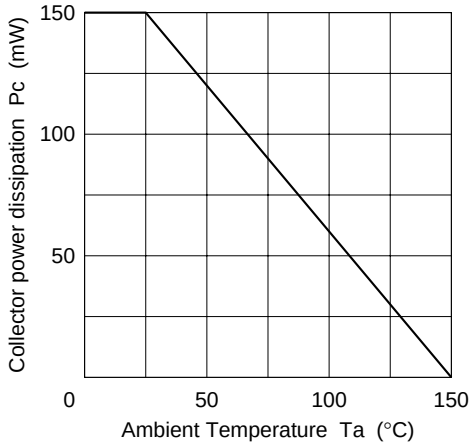
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	–90	—	—	V	I_C = –10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	–90	—	—	V	I_C = –1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	–5	—	—	V	I_E = –10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	–0.1	µA	V_{CB} = –70 V, I_E = 0
Emitter cutoff current	I_{EBO}	—	—	–0.1	µA	V_{EB} = –2 V, I_C = 0
DC current transfer ratio	h_{FE}*[1]	250	—	800		V_{CE} = –12 V, I_C = –2 mA*[2]
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	–0.15	V	I_C = –10 mA, I_B = –1 mA*[2]
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	–1.0	V	I_C = –10 mA, I_B = –1 mA*[2]

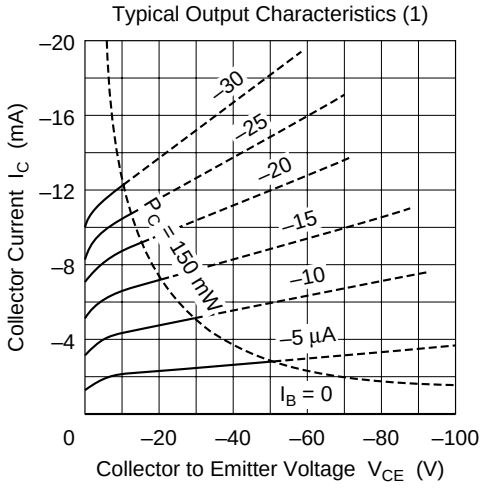
Notes: 1. The 2SA1484 is grouped by h_{FE} as follows.
2. Pulse test

Grade	D	E
Mark	IRD	IRE
h_{FE}	250 to 500	400 to 800

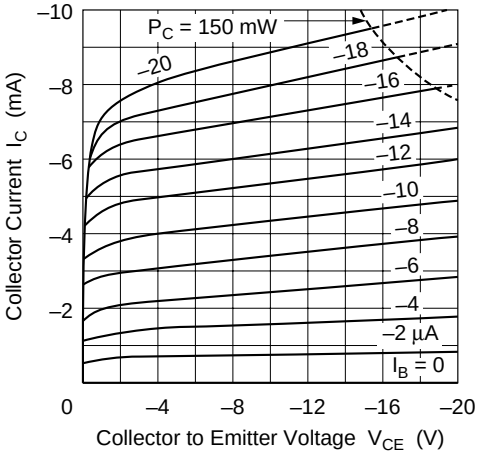
Maximum Collector Dissipation Curve



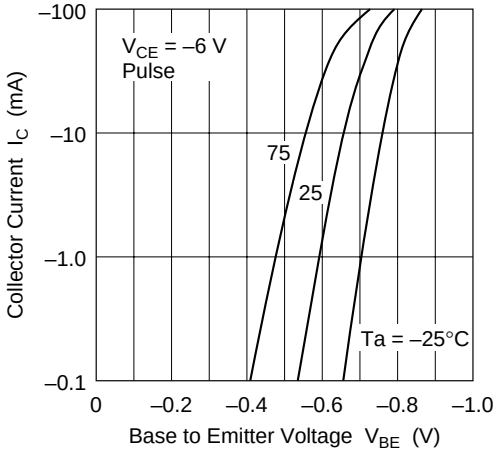
Typical Output Characteristics (1)



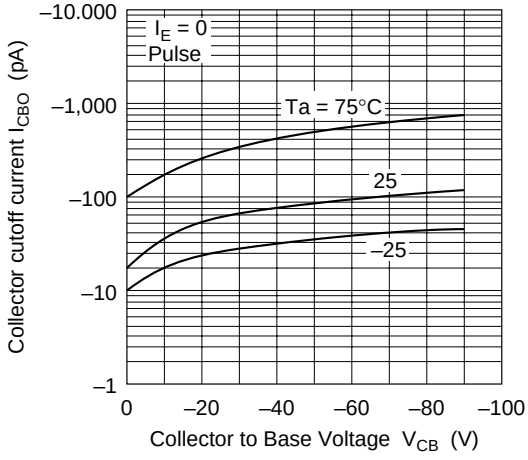
Typical Output Characteristics (2)



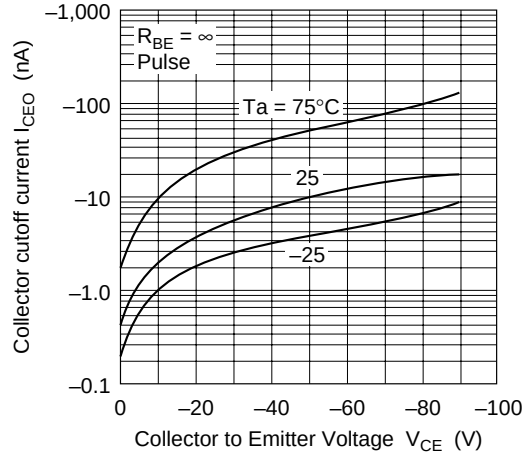
Typical Transfer Characteristics



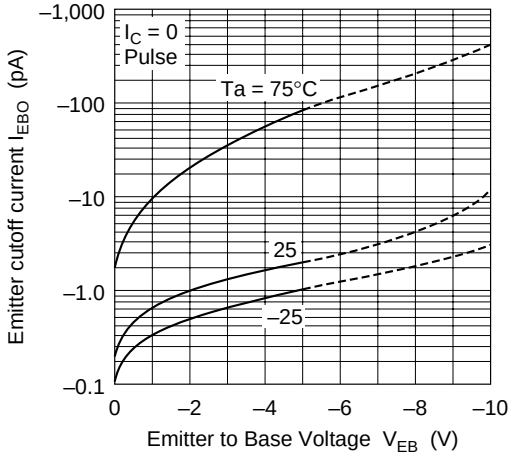
Collector Cutoff Current vs.
Collector to Base Voltage



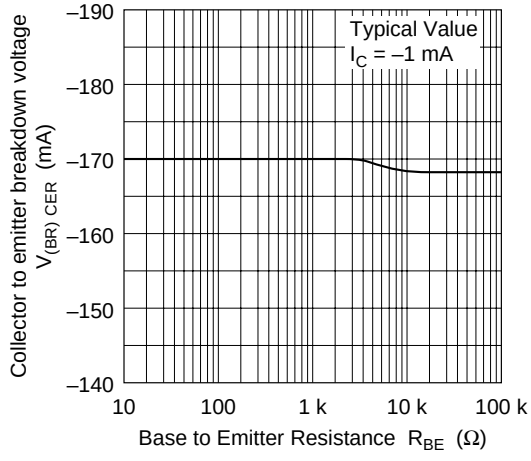
Collector Cutoff Current vs.
Collector to Emitter Voltage



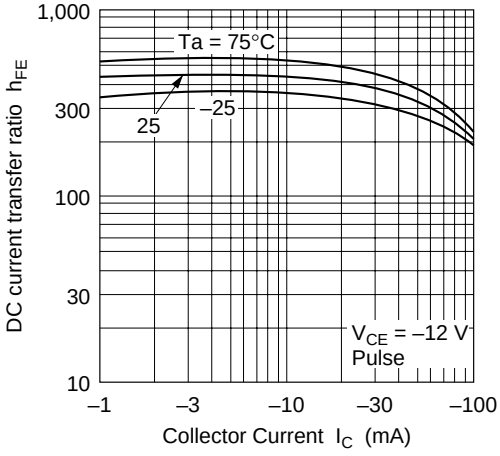
Emitter Cutoff Current vs.
Emitter to Base Voltage



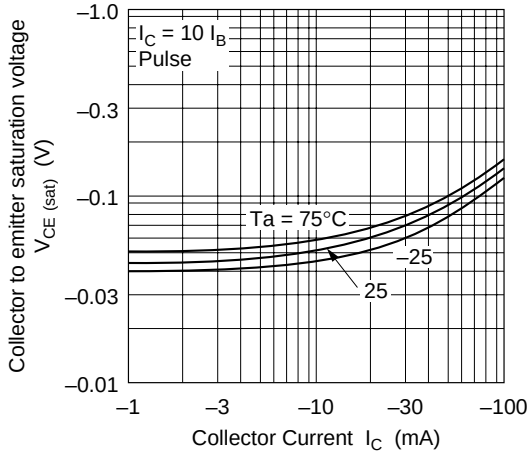
Collector to Emitter Breakdown Voltage vs.
Base to Emitter Resistance



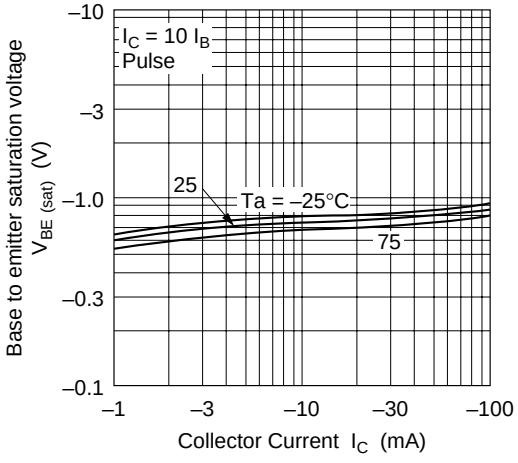
DC Current Transfer Ratio vs. Collector Current



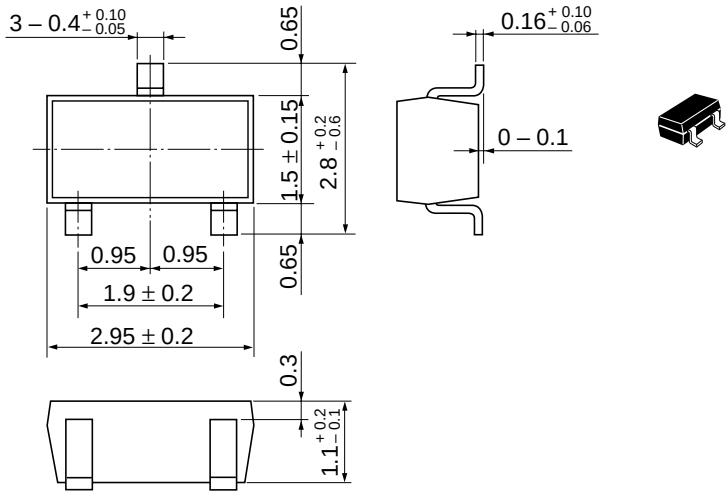
Collector to Emitter Saturation Voltage vs. Collector Current



Base to Emitter Saturation Voltage vs. Collector Current



Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.011 g

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